INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
M4065.051/P[redacted]	09/076,745
Applicant(s)	
Leonard Forbes et al.	
Filing Date	**Group Art Unit**
May 13, 1998	2818

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

JC861 U.S. PTO 09/609813 06/30/00

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

PEB	A	Farid Nemati et al, "A NOVEL HIGH DENSITY, LOW VOLTGE SRAM CELL WITH A VERTICAL NDR DEVICE", Center for Integrated Systems, Stanford University, Stanford, CA, (2 pages)
PEB	B	Hyun-Jin Cho et al, "A NOVEL PILLAR DRAM CELL FOR 4GBIT AND BEYOND", Center for Integrated Systems, Stanford University, Stanford, CA, (2 pages)
X		(For both A and B citations above - published in IEEE 1998, Symposium on VLSI Technology, Honolulu, Hawaii, June 9th and 11th, 1998)

EXAMINER	DATE CONSIDERED
Not Yet Assigned Paul E Brooke	4/4/2001

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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M4065.051/p051	Not Yet Assigned
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LEONARD FORBES ET AL.	
Filing Date	**Group Art Unit**
Concurrently Herewith	N/A

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M4065.051[redacted]1	Not Yet Assigned
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LEONARD FORBES et al.	
Filing Date	**Group Art Unit**
Concurrently Herewith	N/A

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Not Yet Assigned Paul E Brock II	4/4/2001

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Concurrently Herewith	Not Assigned

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*EXAMINER INITIAL	REF	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	No Citations to United States Patent Documents						

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